Renesas Electronics America Inc - R5F363AKNFA#U0 Datasheet

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	M16C/60
Core Size	16-Bit
Speed	20MHz
Connectivity	EBI/EMI, I²C, SIO, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	85
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	31K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-BQFP
Supplier Device Package	100-QFP (14x20)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f363aknfa-u0

1.3 Product List

Table 1.5 lists product information. Figure 1.1 shows the Part No., with Memory Size and Package, and Figure 1.2 and Figure 1.3 shows the Marking Diagram (Top View).

Table 1.5 Product List As of November, 2012

Part No.	ROM Capacity			RAM Capacity	Package Code	Remarks
	Program ROM 1	Program ROM 2	Data flash			
R5F363A6NFA	128 KB	16 KB	4 KB × 2 blocks	12 KB	PRQP0100JD-B	Operating temperature -20°C to 85°C
R5F363A6NFB					PLQP0100KB-A	
R5F363A6NLG					PTLG0100KA-A	
R5F363B6NFE					PLQP0080KB-A	
R5F363A6DFA					PRQP0100JD-B	Operating temperature -40°C to 85°C
R5F363A6DFB					PLQP0100KB-A	
R5F363B6DFE					PLQP0080KB-A	
R5F363AENFA	256 KB	16 KB	4 KB × 2 blocks	20 KB	PRQP0100JD-B	Operating temperature -20°C to 85°C
R5F363AENFB					PLQP0100KB-A	
R5F363AENLG					PTLG0100KA-A	
R5F363BENFE					PLQP0080KB-A	
R5F363AEDFA					PRQP0100JD-B	Operating temperature -40°C to 85°C
R5F363AEDFB					PLQP0100KB-A	
R5F363BEDFE					PLQP0080KB-A	
R5F363AKNFA	384 KB	16 KB	4 KB × 2 blocks	31 KB	PRQP0100JD-B	Operating temperature -20°C to 85°C
R5F363AKNFB					PLQP0100KB-A	
R5F363AKNLG					PTLG0100KA-A	
R5F363AKDFA					PRQP0100JD-B	Operating temperature -40°C to 85°C
R5F363AKDFB					PLQP0100KB-A	
R5F363AMNFA	512 KB	16 KB	4 KB × 2 blocks	31 KB	PRQP0100JD-B	Operating temperature -20°C to 85°C
R5F363AMNFB					PLQP0100KB-A	
R5F363AMNLG					PTLG0100KA-A	
R5F363AMDFA					PRQP0100JD-B	Operating temperature -40°C to 85°C
R5F363AMDFB					PLQP0100KB-A	

(D): Under development
(P): Planning

Previous package codes are as follows:
PRQP0100JD-B: 100P6F-A
PLQP0100KB-A: 100P6Q-A
PTLG0100KA-A: 100F0M
PLQP0080KB-A: 80P6Q-A

Table 1.12 Pin Functions for the 100-Pin Package (3/3)

Signal Name	Pin Name	I/O	Power Supply	Description
UART0 to UART2, UART5 to UART7 I^2C mode	SDA0 to SDA2, SDA5	I/O	VCC1	Serial data I/O.
	SDA6, SDA7	I/O	VCC2	
	SCL0 to SCL2, SCL5	I/O	VCC1	Transmit/receive clock I/O.
	SCL6, SCL7	I/O	VCC2	
Serial interface SI/O3, SI/O4	CLK3, CLK4	I/O	VCC1	Transmit/receive clock I/O.
	SIN3, SIN4	I	VCC1	Serial data input.
	SOUT3, SOUT4	O	VCC1	Serial data output.
Multi-master I^2C-bus interface	SDAMM	I/O	VCC1	Serial data I/O (N-channel open drain output).
	SCLMM	I/O	VCC1	Transmit/receive clock I/O (N-channel open drain output).
CEC I/O	CEC	I/O	VCC1	CEC I/O (N-channel open drain output).
Reference voltage input	VREF	I	VCC1	Reference voltage input for the A/D and D/A converters.
A/D converter	AN0 to AN7	I	VCC1	Analog input.
	AN0_0 to AN0_7 AN2_0 to AN2_7	I	VCC2	
	$\overline{\text{ADTRG}}$	I	VCC1	External trigger input.
	ANEX0, ANEX1	I	VCC1	Extended analog input.
D/A converter	DA0, DA1	O	VCC1	Output for the D/A converter.
I/O ports	P0_0 to P0_7 P1_0 to P1_7 P2_0 to P2_7 P3_0 to P3_7 P4_0 to P4_7 P5_0 to P5_7	I/O	VCC2	8-bit CMOS I/O ports. A direction register determines whether each pin is used as an input port or an output port. A pull-up resistor may be enabled or disabled for input ports in 4-bit units.
	P6_0 to P6_7 P7_0 to P7_7 P8_0 to P8_7 P9_0 to P9_7 P10_0 to P10_7	I/O	VCC1	8-bit I/O ports having equivalent functions to P0. However, P7_0, P7_1, and P8_5 are N-channel open drain output ports. No pull-up resistor is provided. P8_5 is an input port for verifying the $\overline{\text{NMI}}$ pin level and shares a pin with $\overline{\text{NMI}}$.

Table 4.12 SFR Information (12) (1)

Address	Register	Symbol	Reset Value
0300h	Timer B3/B4/B5 Count Start Flag	TBSR	000X XXXXb
0301h			
0302h	Timer A1-1 Register	TA11	XXh
0303h			XXh
0304h	Timer A2-1 Register	TA21	XXh
0305h			XXh
0306h	Timer A4-1 Register	TA41	XXh
0307h			XXh
0308h	Three-Phase PWM Control Register 0	INVC0	00h
0309h	Three-Phase PWM Control Register 1	INVC1	00h
030Ah	Three-Phase Output Buffer Register 0	IDB0	XX11 1111b
030Bh	Three-Phase Output Buffer Register 1	IDB1	XX11 1111b
030Ch	Dead Time Timer	DTT	XXh
030Dh	Timer B2 Interrupt Generation Frequency Set Counter	ICTB2	XXh
030Eh	Position-Data-Retain Function Control Register	PDRF	XXXX 0000b
030Fh			
0310h	Timer B3 Register	TB3	XXh
0311h			XXh
0312h	Timer B4 Register	TB4	XXh
0313h			XXh
0314h	Timer B5 Register	TB5	XXh
0315h			XXh
0316h			
0317h			
0318h	Port Function Control Register	PFCR	0011 1111b
0319h			
031Ah			
031Bh	Timer B3 Mode Register	TB3MR	00XX 0000b
031Ch	Timer B4 Mode Register	TB4MR	00XX 0000b
031Dh	Timer B5 Mode Register	TB5MR	00XX 0000b
031Eh			
031Fh			
0320h	Count Start Flag	TABSR	00h
0321h			
0322h	One-Shot Start Flag	ONSF	00h
0323h	Trigger Select Register	TRGSR	00h
0324h	Increment/Decrement Flag	UDF	00h
0325h			
0326h	Timer A0 Register	TA0	XXh
0327h			XXh
0328h	Timer A1 Register	TA1	XXh
0329h			XXh
032Ah	Timer A2 Register	TA2	XXh
032Bh			XXh
032Ch	Timer A3 Register	TA3	XXh
032Dh			XXh
032Eh	Timer A4 Register	TA4	XXh
032Fh			XXh

X: Undefined

Note:
1. The blank areas are reserved. No access is allowed.

Table 4.18 SFR Information (18) (1)

Address	Register	Symbol	Reset Value
D080h	PMC0 Header Pattern Set Register (Min)	PMC0HDPMIN	0000 0000b
D081h			XXXX X000b
D082h	PMC0 Header Pattern Set Register (Max)	PMC0HDPMAX	0000 0000b
D083h			XXXX X000b
D084h	PMC0 Data 0 Pattern Set Register (Min)	PMC0D0PMIN	00h
D085h	PMC0 Data 0 Pattern Set Register (Max)	PMC0D0PMAX	00h
D086h	PMC0 Data 1 Pattern Set Register (Min)	PMC0D1PMIN	00h
D087h	PMC0 Data 1 Pattern Set Register (Max)	PMC0D1PMAX	00h
D088h	PMC0 Measurements Register	PMC0TIM	00h
D089h			00h
D08Ah			
D08Bh			
D08Ch	PMC0 Receive Data Store Register 0	PMC0DAT0	00h
D08Dh	PMC0 Receive Data Store Register 1	PMC0DAT1	00h
D08Eh	PMC0 Receive Data Store Register 2	PMC0DAT2	00h
D08Fh	PMC0 Receive Data Store Register 3	PMC0DAT3	00h
D090h	PMC0 Receive Data Store Register 4	PMC0DAT4	00h
D091h	PMC0 Receive Data Store Register 5	PMC0DAT5	00h
D092h	PMC0 Receive Bit Count Register	PMC0RBIT	XX00 0000b
D093h			
D094h	PMC1 Header Pattern Set Register (Min)	PMC1HDPMIN	0000 0000b
D095h			XXXX X000b
D096h	PMC1 Header Pattern Set Register (Max)	PMC1HDPMAX	0000 0000b
D097h			XXXX X000b
D098h	PMC1 Data 0 Pattern Set Register (Min)	PMC1D0PMIN	00h
D099h	PMC1 Data 0 Pattern Set Register (Max)	PMC1D0PMAX	00h
D09Ah	PMC1 Data 1 Pattern Set Register (Min)	PMC1D1PMIN	00h
D09Bh	PMC1 Data 1 Pattern Set Register (Max)	PMC1D1PMAX	00h
D09Ch	PMC1 Measurements Register	PMC1TIM	00h
D09Dh			00h
D09Eh			
D09Fh			

X: Undefined

Note:
1. The blank areas are reserved. No access is allowed.

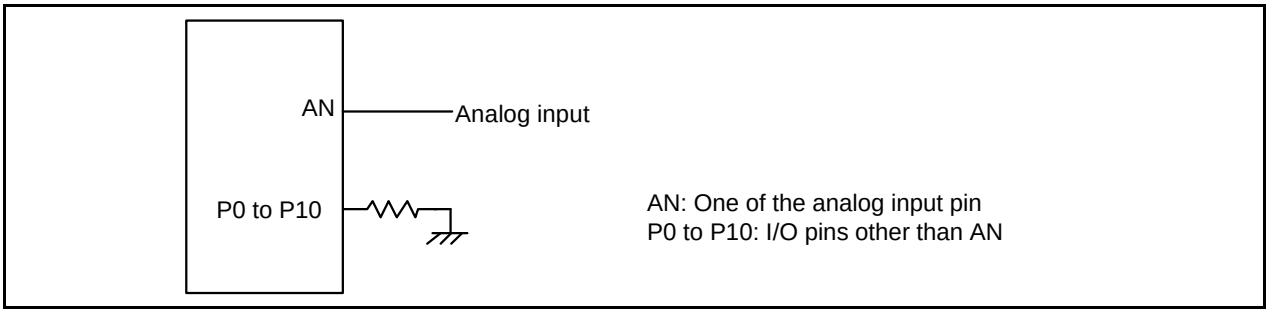


Figure 5.3 A/D Accuracy Measure Circuit

Table 5.7 A/D Conversion Characteristics (2/2) (1)

$AV_{CC} = V_{CC1} = V_{CC2} = V_{REF} = 1.8$ to 5.5 V, $V_{SS} = AV_{SS} = 0$ V at T_{opr} = -20°C to 85°C/-40°C to 85°C unless otherwise specified.

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
ϕAD	A/D operating clock frequency	4.0 V ≤ V_{REF} ≤ AV_{CC} ≤ 5.5 V	2		20	MHz
		3.2 V ≤ V_{REF} ≤ AV_{CC} ≤ 5.5 V	2		16	MHz
		3.0 V ≤ V_{REF} ≤ AV_{CC} ≤ 5.5 V	2		10	MHz
		1.8 V ≤ V_{REF} ≤ AV_{CC} ≤ 5.5 V	2		5	MHz
-	Tolerance level impedance			3		kΩ
D_{NL}	Differential non-linearity error	(4)			±1	LSB
-	Offset error	(4)			±3	LSB
-	Gain error	(4)			±3	LSB
t_{CONV}	10-bit conversion time	V_{CC1} = 5 V, ϕAD = 20 MHz	2.15			µs
t_{SAMP}	Sampling time		0.75			µs
V_{REF}	Reference voltage		1.8		AV_{CC}	V
V_{IA}	Analog input voltage (2), (3)		0		V_{REF}	V

Notes:
1. Use when $AV_{CC} = V_{CC1} = V_{CC2}$.
2. Do not use A/D converter when $V_{CC1} > V_{CC2}$.
3. When analog input voltage is over reference voltage, the result of A/D conversion is 3FFh.
4. Flash memory rewrite disabled. Except for the analog input pin, set the pins to be measured as input ports and connect them to V_{SS}. See Figure 5.3 “A/D Accuracy Measure Circuit”.

5.1.4 D/A Conversion Characteristics

Table 5.8 D/A Conversion Characteristics

$V_{CC1} = AV_{CC} = V_{REF} = 3.0$ to 5.5 V, $V_{SS} = AV_{SS} = 0$ V at T_{opr} = -20°C to 85°C/-40°C to 85°C unless otherwise specified.

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
-	Resolution				8	Bits
-	Absolute Accuracy				2.5	LSB
t_{SU}	Setup Time				3	µs
R_O	Output Resistance		5	6	8.2	kΩ
I_{VREF}	Reference Power Supply Input Current	See Notes 1 and 2			1.5	mA

Notes:
1. This applies when using one D/A converter, with the D/A register for the unused D/A converter set to 00h.
2. The current consumption of the A/D converter is not included. Also, the I_{VREF} of the D/A converter will flow even if the ADSTBY bit in the ADCON1 register is 0 (A/D operation stopped (standby)).

5.1.5 Flash Memory Electrical Characteristics

Table 5.9 CPU Clock When Operating Flash Memory ($f_{(BCLK)}$)

V_{CC1} = 1.8 to 5.5 V, T_{opr} = -20°C to 85°C/-40°C to 85°C unless otherwise specified.

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
-	CPU rewrite mode				10 (1)	MHz
f(SLOW_R)	Slow read mode				5 (3)	MHz
-	Low current consumption read mode			fC(32.768)	35	kHz
-	Data flash read	3.0 V < V_{CC1} ≤ 5.5 V			20 (2)	MHz

Notes:
1. Set the PM17 bit in the PM1 register to 1 (one wait).
2. When the frequency is 1.8 ≤ V_{CC1} ≤ 3.0 V, set the FMR17 bit in the FMR1 register to 0 (one wait) or the PM17 bit in the PM1 register to 1 (one wait)
3. Set the PM17 bit in the PM1 register to 1 (one wait). When using 125 kHz on-chip oscillator clock or sub clock as the CPU clock source, a wait is not necessary.

Table 5.10 Flash Memory (Program ROM 1, 2) Electrical Characteristics

V_{CC1} = 2.7 to 5.5 V at T_{opr} = 0°C to 60°C (option: -40°C to 85°C), unless otherwise specified.

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
-	Program and erase cycles (1), (3), (4)	V_{CC1} = 3.3 V, T_{opr} = 25°C	1,000 (2)			times
-	2 word program time	V_{CC1} = 3.3 V, T_{opr} = 25°C		150	4000	µs
-	Lock bit program time	V_{CC1} = 3.3 V, T_{opr} = 25°C		70	3000	µs
-	Block erase time	V_{CC1} = 3.3 V, T_{opr} = 25°C		0.2	3.0	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend				$5 + \frac{3}{f_{(BCLK)}}$	ms
-	Interval from erase start/restart until following suspend request		0			µs
-	Suspend interval necessary for auto-erasure to complete (7)		20			ms
-	Time from suspend until erase restart				$30 + \frac{1}{f_{(BCLK)}}$	µs
-	Program, erase voltage		2.7		5.5	V
-	Read voltage	T_{opr}= -20°C to 85°C/-40°C to 85°C	2.7		5.5	V
-	Program, erase temperature		0		60	°C
t_{PS}	Flash memory circuit stabilization wait time				50	µs
-	Data hold time (6)	Ambient temperature = 55°C	20			year

Notes:
1. Definition of program and erase cycles:
   The program and erase cycles refer to the number of per-block erasures. If the program and erase cycles are n (n = 1,000), each block can be erased n times. For example, if a block is erased after writing 2 word data 16,384 times, each to a different address, this counts as one program and erase cycles. Data cannot be written to the same address more than once without erasing the block (rewrite prohibited).
2. Cycles to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
3. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. It is advisable to retain data on the erasure cycles of each block and limit the number of erase operations to a certain number.
4. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
5. Customers desiring program/erase failure rate information should contact a Renesas Electronics sales office.
6. The data hold time includes time that the power supply is off or the clock is not supplied.
7. After an erase start or erase restart, if an interval of at least 20 ms is not set before the next suspend request, the erase sequence cannot be completed.

Table 5.11 Flash Memory (Data Flash) Electrical Characteristics

V_{CC1} = 2.7 to 5.5 V at T_{opr} = -20 to 85°C/-40 to 85°C, unless otherwise specified.

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
-	Program and erase cycles (1), (3), (4)	V_{CC1} = 3.3 V, T_{opr} = 25°C	10,000 (2)			times
-	2 word program time	V_{CC1} = 3.3 V, T_{opr} = 25°C		300	4000	µs
-	Lock bit program time	V_{CC1} = 3.3 V, T_{opr} = 25°C		140	3000	µs
-	Block erase time	V_{CC1} = 3.3 V, T_{opr} = 25°C		0.2	3.0	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend				$5 + \frac{3}{f_{(BCLK)}}$	ms
-	Interval from erase start/restart until following suspend request		0			µs
-	Suspend interval necessary for auto-erasure to complete (7)		20			ms
-	Time from suspend until erase restart				$30 + \frac{1}{f_{(BCLK)}}$	µs
-	Program, erase voltage		2.7		5.5	V
-	Read voltage		2.7		5.5	V
-	Program, erase temperature		–20/–40		85	°C
t_{PS}	Flash memory circuit stabilization wait time				50	µs
-	Data hold time (6)	Ambient temperature = 55°C	20			year

Notes:
1. Definition of program and erase cycles
   The program and erase cycles refer to the number of per-block erasures.
   If the program and erase cycles are n (n = 10,000), each block can be erased n times.
   For example, if a 4 KB block is erased after writing 2 word data 1,024 times, each to a different address, this counts as one program and erase cycles. Data cannot be written to the same address more than once without erasing the block (rewrite prohibited).
2. Cycles to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
3. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 256 groups before erasing them all in one operation. In addition, averaging the erasure cycles between blocks A and B can further reduce the actual erasure cycles. It is also advisable to retain data on the erasure cycles of each block and limit the number of erase operations to a certain number.
4. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
5. Customers desiring program/erase failure rate information should contact a Renesas Electronics sales office.
6. The data hold time includes time that the power supply is off or the clock is not supplied.
7. After an erase start or erase restart, if an interval of at least 20 ms is not set before the next suspend request, the erase sequence cannot be completed.

Table 5.14 Voltage Detector 2 Electrical Characteristics

The measurement condition is V_{CC1} = 1.8 to 5.5 V, T_{opr} = -20°C to 85°C/-40°C to 85°C, unless otherwise specified.

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level Vdet2_0	When V_{CC1} is falling	3.70	4.00	4.30	V
-	Hysteresis width at the rising of V_{CC1} in voltage detector 2			0.15		V
-	Voltage detector 2 response time (2)	When V_{CC1} falls from 5 V to (Vdet2_0 - 0.1) V			200	µs
-	Voltage detector self power consumption	VC27 = 1, V_{CC1} = 5.0 V		1.7		µA
$t_{d(E-A)}$	Waiting time until voltage detector operation starts (1)				100	µs

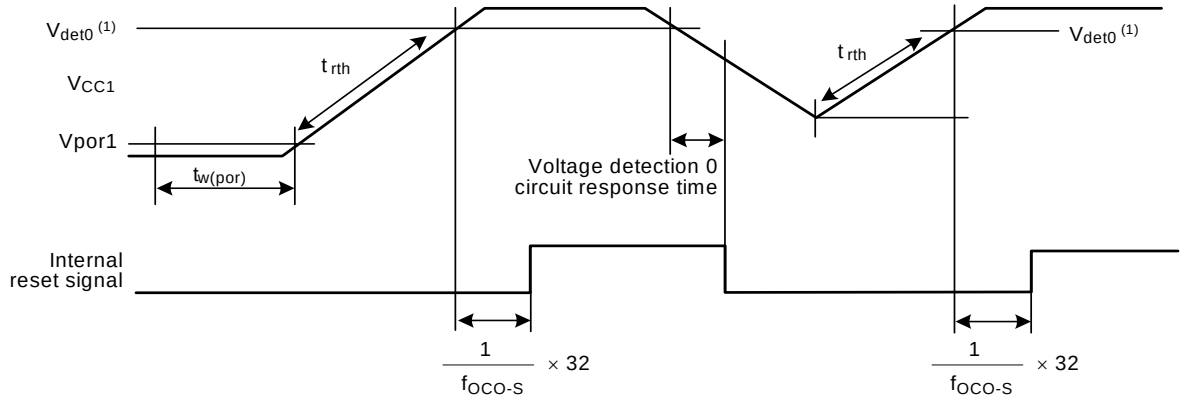
Notes:
1. Necessary time until the voltage detector operates after setting to 1 again after setting the VC27 bit in the VCR2 register to 0.
2. Time from when passing the V_{det2} until when a voltage monitor 2 reset is generated.

Table 5.15 Power-On Reset Circuit

The measurement condition is V_{CC1} = 2.0 to 5.5 V, T_{opr} = -20°C to 85°C/ -40°C to 85°C, unless otherwise specified.

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por1}	Voltage at which power-on reset enabled (1)				0.5	V
t_{rth}	External power V_{CC1} rise gradient		2.0		50000	mV/ms
$t_{w(por)}$	Time necessary to enable power-on reset		300			ms

Note:
1. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVDAS bit in the OFS1 address to 0. Also, set the VDSEL1 bit to 0 (Vdet0_2).



Note:
1. V_{det0} indicates the voltage detection level of the voltage detection 0 circuit.

Figure 5.4 Power-On Reset Circuit Electrical Characteristics

$V_{CC1} = V_{CC2} = 5\ V$

Table 5.20 Electrical Characteristics (2) (1)

$V_{CC1} = V_{CC2} = 4.2$ to $5.5\ V$, $V_{SS} = 0\ V$ at $T_{opr} = -20°C$ to $85°C/-40°C$ to $85°C$, $f_{(BCLK)} = 20$ MHz unless otherwise specified.

Symbol	Parameter		Measuring Condition	Standard			Unit
				Min.	Typ.	Max.	
$V_{T+} - V_{T-}$	Hysteresis	HOLD, RDY, TA0IN to TA4IN, TB0IN to TB5IN, INT0 to INT7, NMI, ADTRG, CTS0 to CTS2, CTS5 to CTS7, SCL0 to SCL2, SCL5 to SCL7, SDA0 to SDA2, SDA5 to SDA7, CLK0 to CLK7, TA0OUT to TA4OUT, KI0 to KI7, RXD0 to RXD2, RXD5 to RXD7, SIN3, SIN4, SD, PMC0, PMC1, SCLMM, SDAMM, CEC, ZP, IDU, IDV, IDW		0.5		2.0	V
$V_{T+} - V_{T-}$	Hysteresis	RESET		0.5		2.5	V
I_{IH}	High input current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7 XIN, RESET, CNVSS, BYTE	$V_I = 5\ V$			5.0	µA
I_{IL}	Low input current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7 XIN, RESET, CNVSS, BYTE	$V_I = 0\ V$			–5.0	µA
R_{PULLUP}	Pull-up resistance	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7	$V_I = 0\ V$	30	50	170	kΩ
R_{fXIN}	Feedback resistance XIN				0.8		MΩ
R_{fXCIN}	Feedback resistance XCIN				8		MΩ
V_{RAM}	RAM retention voltage		In stop mode	1.8			V

Note:
1. When $V_{CC1} \neq V_{CC2}$, refer to 5 V, 3 V, or 1.8 V standard depending on the voltage.

$V_{CC1} = V_{CC2} = 5\ V$

Table 5.21 Electrical Characteristics (3)

$V_{CC1} = V_{CC2} = 4.2$ to 5.5 V, $V_{SS} = 0$ V at $T_{opr} = -20°C$ to 85°C/−40°C to 85°C, $f_{(BCLK)} = 20$ MHz unless otherwise specified.

Symbol	Parameter	Measuring Condition		Standard			Unit
				Min.	Typ.	Max.	
I_{CC}	Power supply current In single-chip, mode, the output pin are open and other pins are V_{SS}	High-speed mode	$f_{(BCLK)}$ = 20 MHz (no division) XIN = 20 MHz (square wave) 125 kHz on-chip oscillator stopped CM15 = 1 (drive capacity High) A/D converter stopped		10.7		mA
			$f_{(BCLK)}$ =20 MHz (no division) XIN = 20 MHz (square wave) 125 kHz on-chip oscillator stopped CM15 = 1 (drive capacity High) A/D converter operating (2)		11.4		mA
			$f_{(BCLK)}$ = 20 MHz XIN = 20 MHz (square wave) 125 kHz on-chip oscillator stopped CM15 = 0 (drive capacity Low) A/D converter stopped		10.1		mA
			$f_{(BCLK)}$ = 20 MHz (no division) XIN = 20 MHz (square wave) 125 kHz on-chip oscillator stopped CM15 = 1 (drive capacity High) PCLKSTP1 = FF (peripheral clock stop)		9.1		mA
			$f_{(BCLK)}$ = 20 MHz (no division) XIN = 20 MHz (square wave) 125 kHz on-chip oscillator stopped CM15 = 0 (drive capacity Low) PCLKSTP1 = FF (peripheral clock stopped)		8.5		mA
		40 MHz on-chip oscillator mode	Main clock stopped 40 MHz on-chip oscillator on, divide-by-2 ($f_{(BCLK)}$ = 20 MHz) 125 kHz on-chip oscillator stopped		9.0		mA
		125 kHz on-chip oscillator mode	Main clock stopped 40 MHz on-chip oscillator stopped, 125 kHz on-chip oscillator on, no division FMR22 = 1 (slow read mode)		450.0		µA
		Low-power mode	$f_{(BCLK)}$ = 32 kHz FMR22 = FMR23 = 1 (in low current consumption read mode) On flash memory (1)		80.0		µA
		Wait mode	$f_{(BCLK)}$ = 32 kHz Main clock stopped 40 MHz on-chip oscillator stopped 125 kHz on-chip oscillator on PM25 = 1 (peripheral function clock fC operating) T_{opr} = 25°C Real-time clock operating		5.6		µA
			$f_{(BCLK)}$ = 32 kHz Main clock stopped 40 MHz on-chip oscillator stopped 125 kHz on-chip oscillator stopped PM25 = 0 (peripheral function clock fC stopped) T_{opr} = 25°C		5.3		µA
		Stop mode	T_{opr} = 25°C		2.4		µA
		During flash memory program	$f_{(BCLK)}$ = 10 MHz, PM17 = 1 (one wait) V_{CC1} = 5.0 V		20.0		mA
		During flash memory erase	$f_{(BCLK)}$ = 10 MHz, PM17 = 1 (one wait) V_{CC1} = 5.0 V		30.0		mA

Notes:
1. This indicates the memory in which the program to be executed exists.
2. A/D conversion is executed in repeat mode.

$V_{CC1} = V_{CC2} = 5\ V$

Timing Requirements

($V_{CC1} = V_{CC2} = 5$ V, $V_{SS} = 0$ V, at T_{opr} = -20°C to 85°C/-40°C to 85°C unless otherwise specified)

5.2.2.7 Multi-master I²C-bus

Table 5.34 Multi-master I²C-bus

Symbol	Parameter	Standard Clock Mode		Fast-mode		Unit
		Min.	Max.	Min.	Max.	
t_{BUF}	Bus free time	4.7		1.3		µs
$t_{HD;STA}$	Hold time in start condition	4.0		0.6		µs
t_{LOW}	Hold time in SCL clock 0 status	4.7		1.3		µs
t_R	SCL, SDA signals' rising time		1000	20 + 0.1 Cb	300	ns
$t_{HD;DAT}$	Data hold time	0		0	0.9	µs
t_{HIGH}	Hold time in SCL clock 1 status	4.0		0.6		µs
f_F	SCL, SDA signals' falling time		300	20 + 0.1 Cb	300	ns
$t_{su;DAT}$	Data setup time	250		100		ns
$t_{su;STA}$	Setup time in restart condition	4.7		0.6		µs
$t_{su;STO}$	Stop condition setup time	4.0		0.6		µs

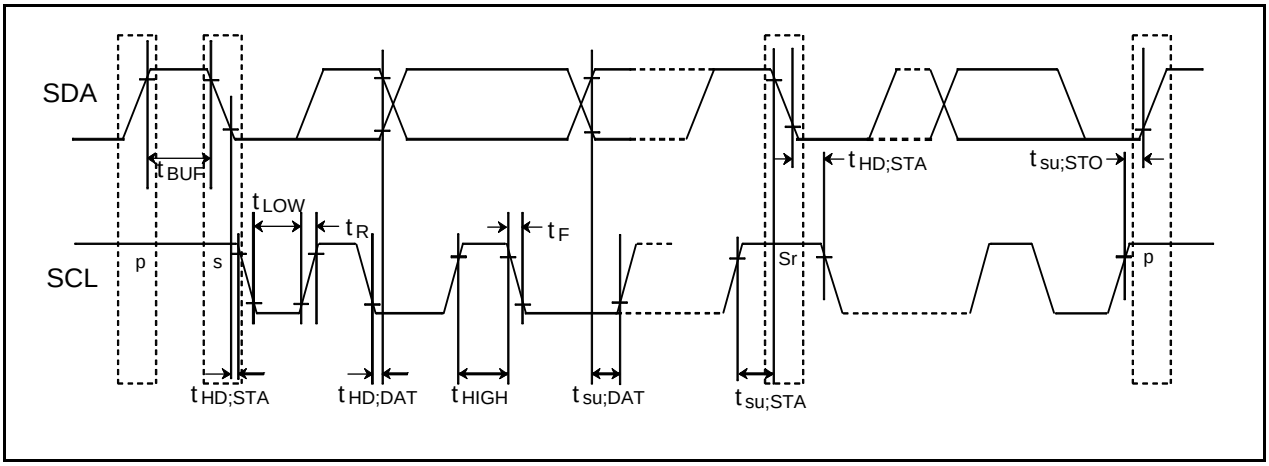
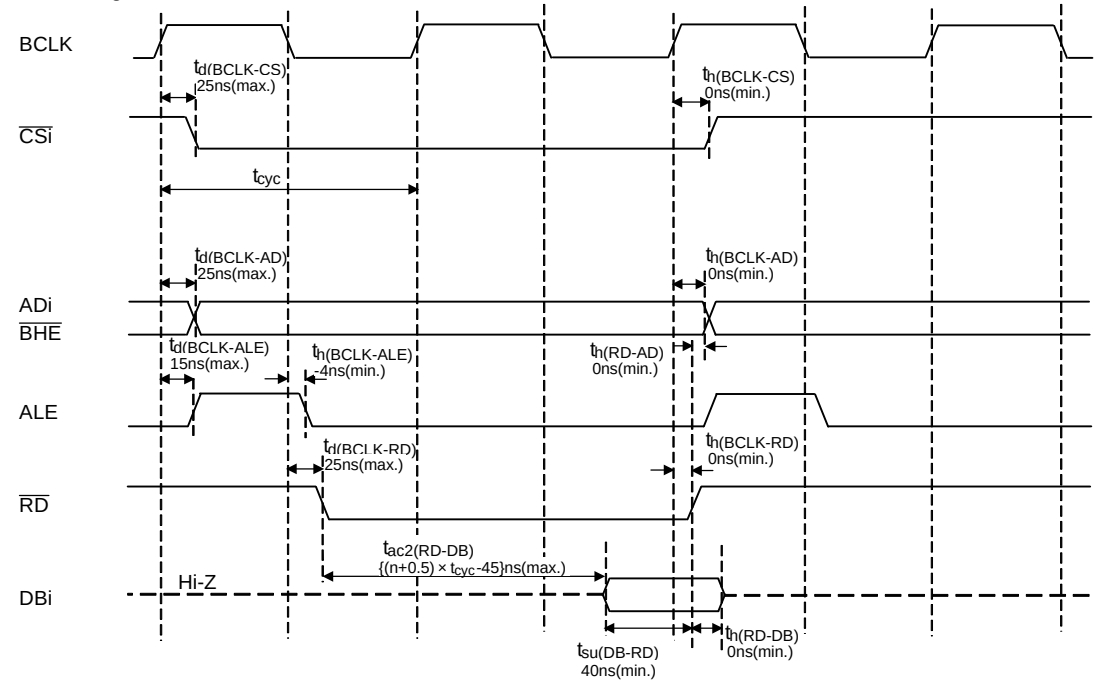


Figure 5.13 Multi-master I²C-bus

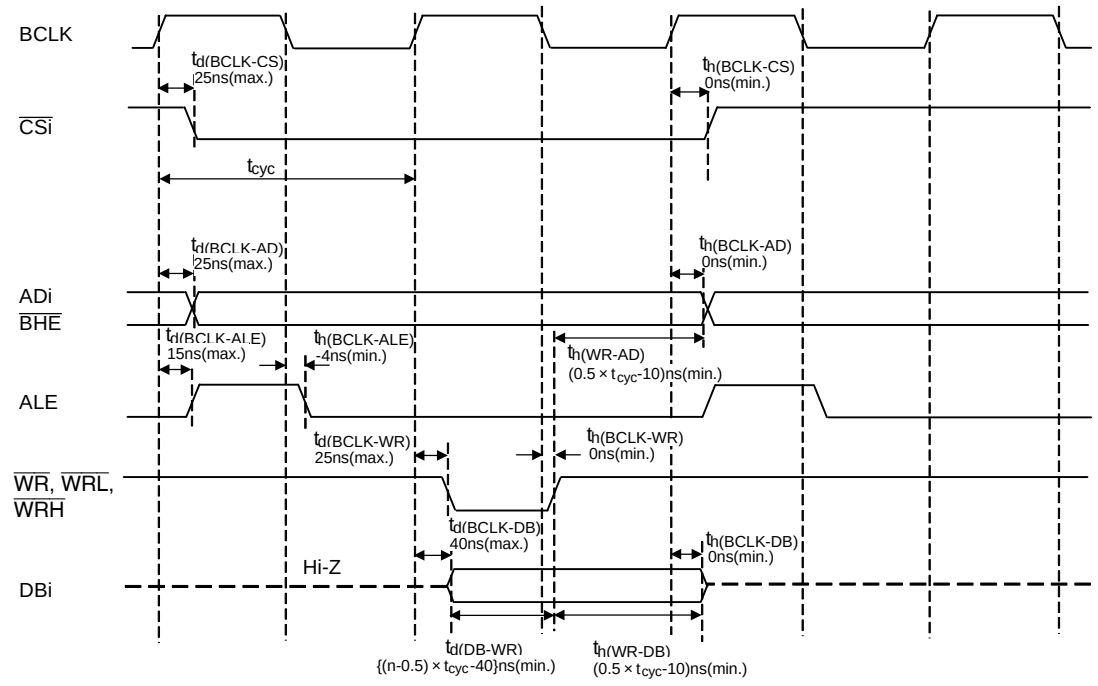
Memory Expansion Mode and Microprocessor Mode
(in 1 to 3 waits setting and when accessing external area)

$V_{CC1} = V_{CC2} = 5V$

Read timing



Write timing



$$t_{cyc} = \frac{1}{f_{(BCLK)}}$$

Measuring conditions

- $V_{CC1} = V_{CC2} = 5V$
- Input timing voltage: $V_{IL} = 0.8$ V, $V_{IH} = 2.0$ V
- Output timing voltage: $V_{OL} = 0.4$ V, $V_{OH} = 2.4$ V

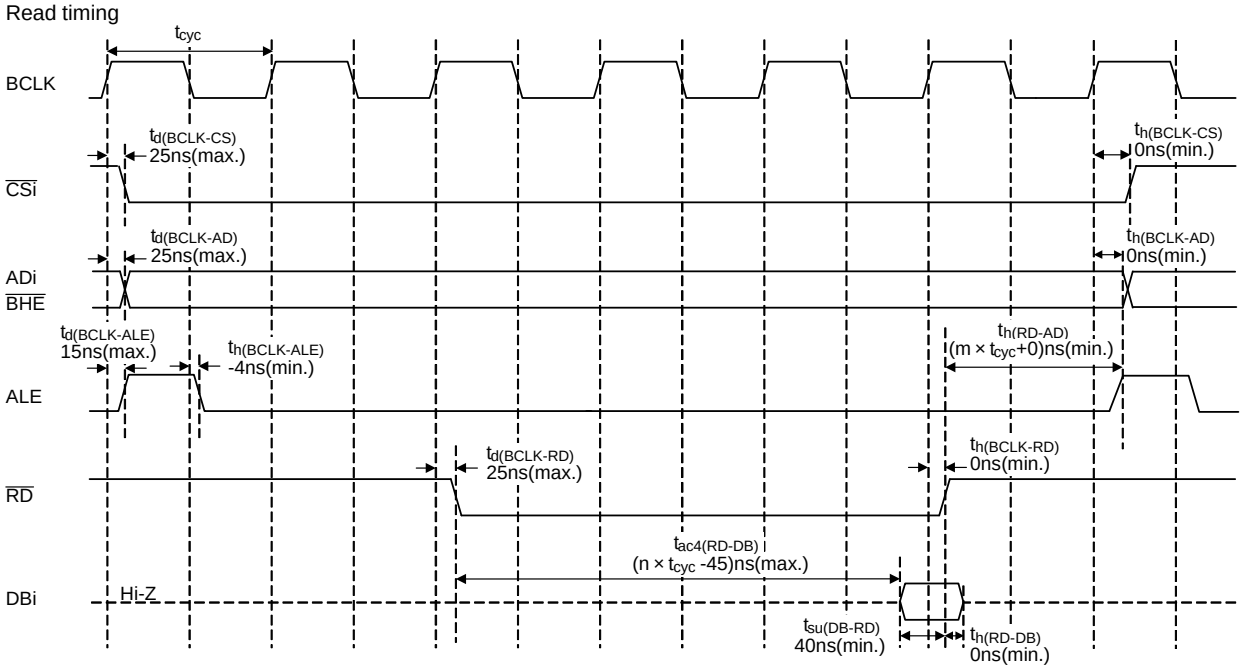
n: 1 (when 1 wait)
2 (when 2 waits)
3 (when 3 waits)

Figure 5.17 Timing Diagram

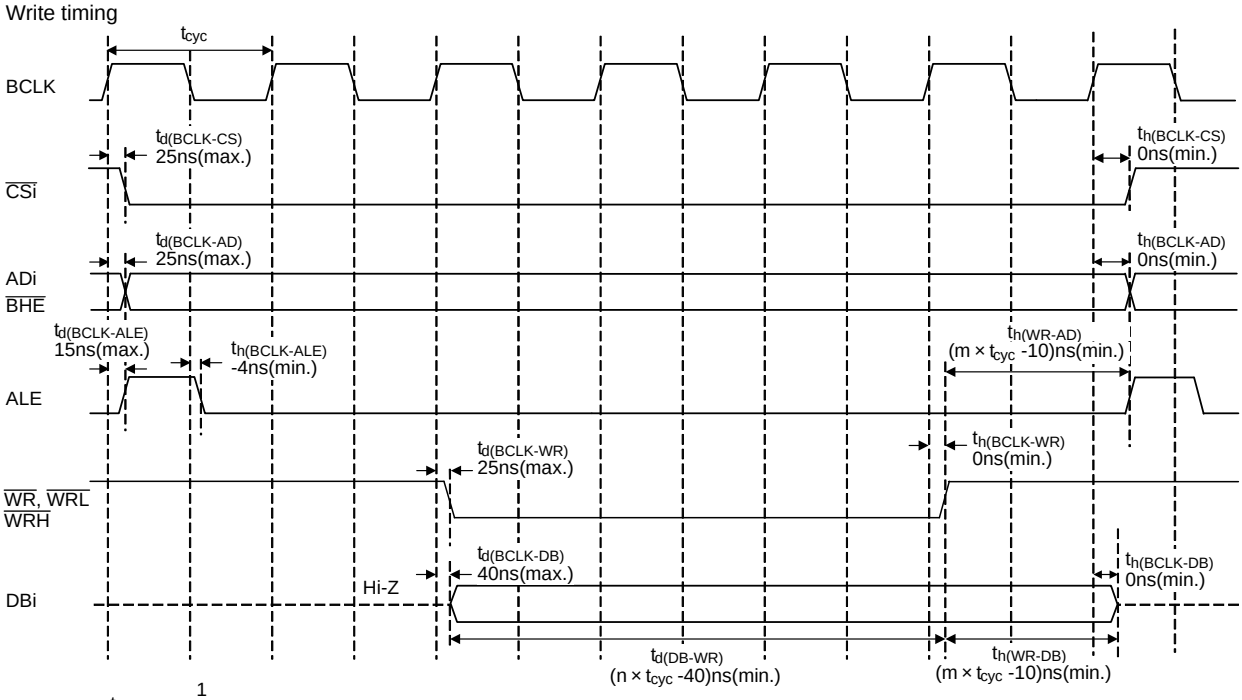
Memory Expansion Mode and Microprocessor Mode
(in wait state setting 2 ϕ + 3 ϕ, 2 ϕ + 4 ϕ, 3ϕ + 4 ϕ, and 4 ϕ + 5 ϕ, and
when inserting 1 to 3 recovery cycles and accessing external area)

$V_{CC1} = V_{CC2} = 5V$

Read timing



Write timing



$$t_{cyc} = \frac{1}{f(BCLK)}$$

Measuring conditions

- $V_{CC1} = V_{CC2} = 5V$
- Input timing voltage: V_{IL} = 0.8 V, V_{IH} = 2.0 V
- Output timing voltage: V_{OL} = 0.4 V, V_{OH} = 2.4 V

n: 3 (when 2 ϕ + 3 ϕ)
4 (when 2 ϕ + 4 ϕ or 3 ϕ + 4 ϕ)
5 (when 4 ϕ + 5 ϕ)

m: 1 (when 1 recovery cycle inserted)
2 (when 2 recovery cycles inserted)
3 (when 3 recovery cycles inserted)

Figure 5.20 Timing Diagram

5.3 Electrical Characteristics (V_{CC1} = V_{CC2} = 3 V)

5.3.1 Electrical Characteristics

V_{CC1} = V_{CC2} = 3 V

Table 5.41 Electrical Characteristics (1) [1]

V_{CC1} = V_{CC2} = 2.7 to 3.3 V, V_{SS} = 0 V at T_{opr} = -20°C to 85°C/-40°C to 85°C, $f_{(BCLK)}$ = 20 MHz unless otherwise specified.

Symbol	Parameter			Measuring Condition	Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	High output voltage	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7		I_{OH} = –1 mA	V_{CC1} – 0.5		V_{CC1}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7		I_{OH} = –1 mA	V_{CC2} – 0.5		V_{CC2}	
V_{OH}	High output voltage XOUT		HIGHPOWER	I_{OH} = –0.1 mA	V_{CC1} – 0.5		V_{CC1}	V
			LOWPOWER	I_{OH} = –50 µA	V_{CC1} – 0.5		V_{CC1}	
	High output voltage XCOUT			With no load applied		1.5		V
V_{OL}	Low output voltage	P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7		I_{OL} = 1 mA			0.5	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7		I_{OL} = 1 mA			0.5	
		CEC		I_{OL} = 1 mA		0	0.5	V
V_{OL}	Low output voltage XOUT		HIGHPOWER	I_{OL} = 0.1 mA			0.5	V
			LOWPOWER	I_{OL} = 50 µA			0.5	
	Low output voltage XCOUT			With no load applied		0		V
V_{T+}-V_{T-}	Hysteresis	$\overline{HOLD}$, $\overline{RDY}$, TA0IN to TA4IN, TB0IN to TB5IN, $\overline{INT0}$ to $\overline{INT7}$, $\overline{NMI}$, $\overline{ADTRG}$, $\overline{CTS0}$ to $\overline{CTS2}$, $\overline{CTS5}$ to $\overline{CTS7}$, SCL0 to SCL2, SCL5 to SCL7, SDA0 to SDA2, SDA5 to SDA7, CLK0 to CLK7, TA0OUT to TA4OUT, $\overline{KI0}$ to $\overline{KI7}$, RXD0 to RXD2, RXD5 to RXD7, SIN3, SIN4, $\overline{SD}$, PMC0, PMC1, SCLMM, SDAMM, ZP, IDU, IDV, IDW			0.2		1.0	V
		CEC			0.2	0.5	1.0	V
		$\overline{RESET}$			0.2		1.8	V
I_{IH}	High input current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7 XIN, $\overline{RESET}$, CNVSS, BYTE		V_I = 3 V			4.0	µA
–	Leakage current in powered-off state		CEC	V_{CC1} = 0 V			1.8	µA
I_{IL}	Low input current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7 XIN, $\overline{RESET}$, CNVSS, BYTE		V_I = 0 V			–4.0	µA
R_{PULLUP}	Pull-up resistance	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7		V_I = 0 V	50	100	500	kΩ
R_{fXIN}	Feedback resistance XIN					0.8		MΩ
R_{fXCIN}	Feedback resistance XCIN					8		MΩ
V_{RAM}	RAM retention voltage			In stop mode	1.8			V

Note:
1. When $V_{CC1} \neq V_{CC2}$, refer to 5 V, 3 V, or 1.8 V standard depending on the voltage.

$V_{CC1} = V_{CC2} = 3\ V$

Timing Requirements

($V_{CC1} = V_{CC2} = 3$ V, $V_{SS} = 0$ V, at $T_{opr} = -20°C$ to 85°C/-40°C to 85°C unless otherwise specified)

5.3.2.4 Timer B Input

Table 5.50 Timer B Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN input cycle time (counted on one edge)	150		ns
$t_{w(TBH)}$	TBiIN input high pulse width (counted on one edge)	60		ns
$t_{w(TBL)}$	TBiIN input low pulse width (counted on one edge)	60		ns
$t_{c(TB)}$	TBiIN input cycle time (counted on both edges)	300		ns
$t_{w(TBH)}$	TBiIN input high pulse width (counted on both edges)	120		ns
$t_{w(TBL)}$	TBiIN input low pulse width (counted on both edges)	120		ns

Table 5.51 Timer B Input (Pulse Period Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN input cycle time	600		ns
$t_{w(TBH)}$	TBiIN input high pulse width	300		ns
$t_{w(TBL)}$	TBiIN input low pulse width	300		ns

Table 5.52 Timer B Input (Pulse Width Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN input cycle time	600		ns
$t_{w(TBH)}$	TBiIN input high pulse width	300		ns
$t^{w(TBL)}$	TBiIN input low pulse width	300		ns

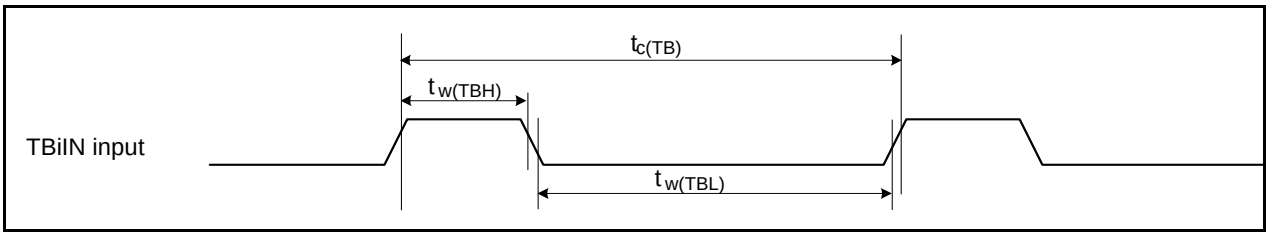


Figure 5.25 Timer B Input

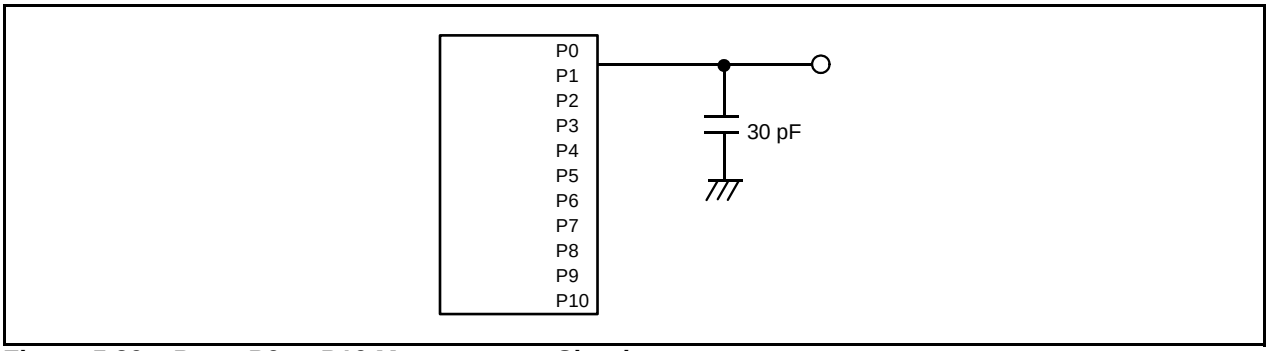


Figure 5.30 Ports P0 to P10 Measurement Circuit

$V_{CC1} = V_{CC2} = 3\ V$

Switching Characteristics

($V_{CC1} = V_{CC2} = 3\ V$, $V_{SS} = 0\ V$, at T_{opr} = -20°C to 85°C/-40°C to 85°C unless otherwise specified)

5.3.4.3 In 2 or 3 Waits Setting, and When Accessing External Area and Using Multiplexed Bus

Table 5.59 Memory Expansion Mode and Microprocessor Mode (in 2 or 3 Waits Setting, and When Accessing External Area and Using Multiplexed Bus) (5)

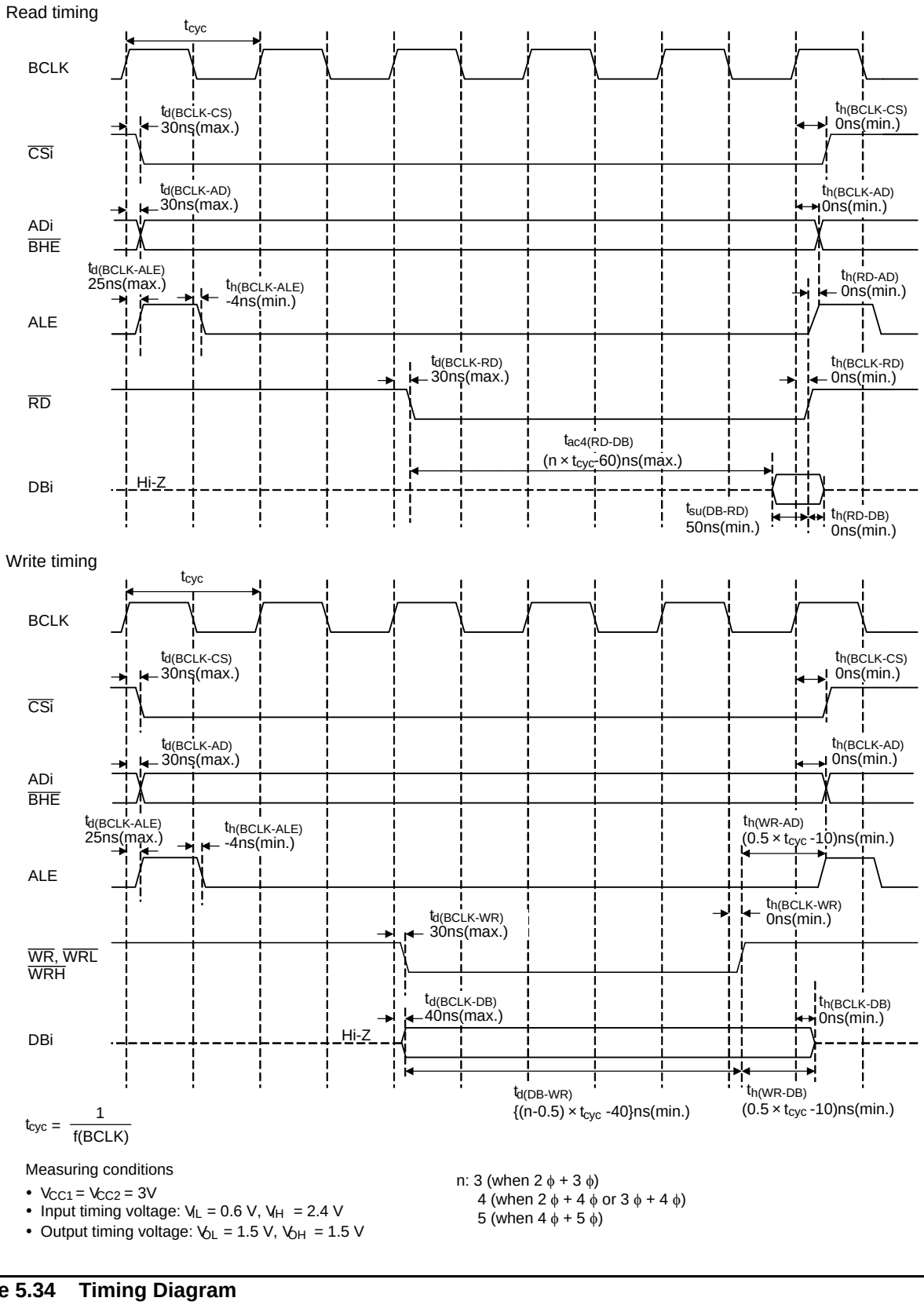
Symbol	Parameter	Measuring Condition	Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address output delay time	See Figure 5.30		50	ns
$t_{h(BCLK-AD)}$	Address output hold time (in relation to BCLK)		0		ns
$t_{h(RD-AD)}$	Address output hold time (in relation to RD)		(Note 1)		ns
$t_{h(WR-AD)}$	Address output hold time (in relation to WR)		(Note 1)		ns
$t_{d(BCLK-CS)}$	Chip select output delay time			50	ns
$t_{h(BCLK-CS)}$	Chip select output hold time (in relation to BCLK)		0		ns
$t_{h(RD-CS)}$	Chip select output hold time (in relation to RD)		(Note 1)		ns
$t_{h(WR-CS)}$	Chip select output hold time (in relation to WR)		(Note 1)		ns
$t_{d(BCLK-RD)}$	RD signal output delay time			40	ns
$t_{h(BCLK-RD)}$	RD signal output hold time		0		ns
$t_{d(BCLK-WR)}$	WR signal output delay time			40	ns
$t_{h(BCLK-WR)}$	WR signal output hold time		0		ns
$t_{d(BCLK-DB)}$	Data output delay time (in relation to BCLK)			50	ns
$t_{h(BCLK-DB)}$	Data output hold time (in relation to BCLK)		0		ns
$t_{d(DB-WR)}$	Data output delay time (in relation to WR)		(Note 2)		ns
$t_{h(WR-DB)}$	Data output hold time (in relation to WR)		(Note 1)		ns
$t_{d(BCLK-ALE)}$	ALE signal output delay time (in relation to BCLK)			25	ns
$t_{h(BCLK-ALE)}$	ALE signal output hold time (in relation to BCLK)		–4		ns
$t_{d(AD-ALE)}$	ALE signal output delay time (in relation to Address)		(Note 3)		ns
$t_{h(AD-ALE)}$	ALE signal output hold time (in relation to Address)		(Note 4)		ns
$t_{d(AD-RD)}$	RD signal output delay from the end of address		0		ns
$t_{d(AD-WR)}$	WR signal output delay from the end of address		0		ns
$t_{dz(RD-AD)}$	Address output floating start time			8	ns

Notes:

1. Calculated according to the BCLK frequency as follows: $\frac{0.5 \times 10^9}{f_{(BCLK)}} - 10[ns]$
2. Calculated according to the BCLK frequency as follows:
   $\frac{(n - 0.5) \times 10^9}{f_{(BCLK)}} - 50[ns]$ n is 2 for 2 waits setting, 3 for 3 waits setting.
3. Calculated according to the BCLK frequency as follows: $\frac{0.5 \times 10^9}{f_{(BCLK)}} - 40[ns]$
4. Calculated according to the BCLK frequency as follows: $\frac{0.5 \times 10^9}{f_{(BCLK)}} - 15[ns]$
5. When using multiplexed bus, set $f_{(BCLK)}$ 12.5 MHz or less.

Memory Expansion Mode, Microprocessor Mode
(in wait state setting 2 ϕ + 3 ϕ, 2 ϕ + 4 ϕ, 3ϕ + 4 ϕ, and 4 ϕ + 5 ϕ, and when accessing external area)

$V_{CC1} = V_{CC2} = 3V$



$t_{cyc} = \frac{1}{f(BCLK)}$

Measuring conditions

- $V_{CC1} = V_{CC2} = 3V$
- Input timing voltage: $V_{IL} = 0.6$ V, $V_{IH} = 2.4$ V
- Output timing voltage: $V_{OL} = 1.5$ V, $V_{OH} = 1.5$ V

n: 3 (when 2 ϕ + 3 ϕ)
4 (when 2 ϕ + 4 ϕ or 3 ϕ + 4 ϕ)
5 (when 4 ϕ + 5 ϕ)

Figure 5.34 Timing Diagram

$V_{CC1} = V_{CC2} = 1.8\ V$

Timing Requirements

($V_{CC1} = V_{CC2} = 1.8$ V, $V_{SS} = 0$ V, at $T_{opr} = -20°C$ to 85°C/-40°C to 85°C unless otherwise specified)

5.4.2.5 Serial Interface

Table 5.75 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	800		ns
$t_{w(CKH)}$	CLKi input high pulse width	400		ns
$t_{w(CKL)}$	CLKi input low pulse width	400		ns
$t_{d(C-Q)}$	TXDi output delay time		240	ns
$t_{h(C-Q)}$	TXDi hold time	0		ns
$t_{su(D-C)}$	RXDi input setup time	200		ns
$t_{h(C-D)}$	RXDi input hold time	90		ns

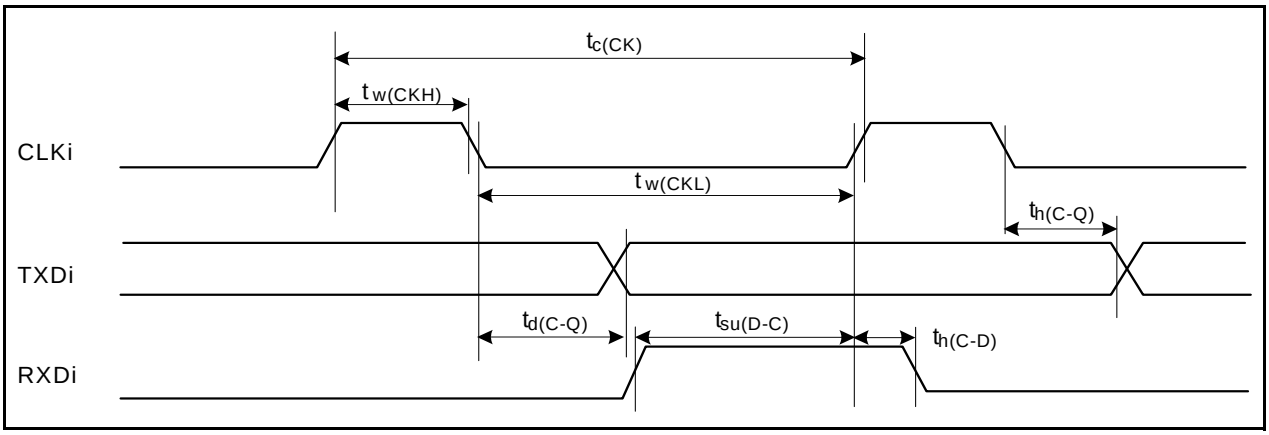


Figure 5.41 Serial Interface

5.4.2.6 External Interrupt $\overline{INTi}$ Input

Table 5.76 External Interrupt $\overline{INTi}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{INTi}$ input high pulse width	1000		ns
$t_{w(INL)}$	$\overline{INTi}$ input low pulse width	1000		ns
tr(INT)	$\overline{INTi}$ input rising time		100	µs
tf(INT)	$\overline{INTi}$ input falling time		100	µs

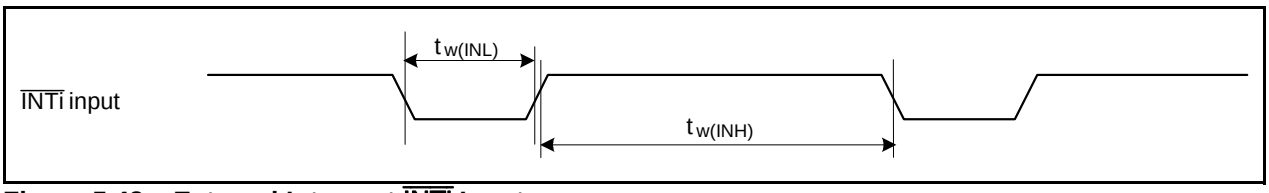


Figure 5.42 External Interrupt $\overline{INTi}$ Input

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